

AMENDMENTS TO THE SPECIFICATION

Amend paragraph [0022] as follows:

[0022] In the description that follows, the term “impurity” is used to refer to a “dopant” or “non-dopant” for incorporation into a semiconductor thin film. As utilized in this description, a “dopant” is an element which alters the equilibrium electron or hole concentration in an intrinsic semiconductor film. Dopant elements comprise, for example, boron (B), phosphorous (Ph) phosphorous (P) and arsenic (As). A “non-dopant” is an element that does not add to or subtract from the equilibrium carrier concentration in an intrinsic semiconductor film. Additionally, a non-dopant does not alter the density or location of states of the intrinsic semiconductor film. Non-dopant elements comprise, for example, carbon (C) and germanium (Ge). While an embodiment of the invention will be described in terms of incorporating a dopant, such as As, in an emitter region and a non-dopant, such as C, in a base region, other dopants and non-dopants could also be so incorporated into the emitter and base regions. Also, dopants and/or non-dopants could also be so incorporated into other regions of the SiGe bipolar transistor such as, for example, the collector region.